74AHC125-Q100; 74AHCT125-Q100

Quad buffer/line driver; 3-state

Rev. 1 — 5 June 2012 Product data sheet

1. General description

The 74AHC125-Q100; 74AHCT125-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard JESD7-A.

The 74AHC125-Q100; 74AHCT125-Q100 provides four non-inverting buffer/line drivers with 3-state outputs. The 3-state outputs (nY) are controlled by the output enable input ($n\overline{OE}$). A HIGH at $n\overline{OE}$ causes the outputs to assume a high-impedance OFF-state.

The 74AHC125-Q100; 74AHCT125-Q100 is identical to the 74AHC126-Q100; 74AHCT126-Q100 but has active LOW enable inputs.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Balanced propagation delays
- All inputs have a Schmitt trigger action
- Inputs accept voltages higher than V_{CC}
- For 74AHC125-Q100: CMOS input levels
- For 74AHCT125-Q100: TTL input levels
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC125D-Q100	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHCT125D-Q100				
74AHC125PW-Q100	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHCT125PW-Q100				
74AHC125BQ-Q100	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1
74AHCT125BQ-Q100				

4. Functional diagram

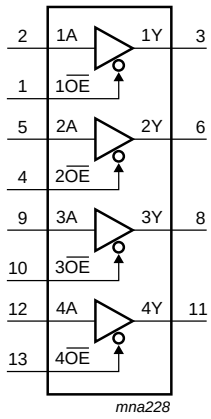


Fig 1. Logic symbol

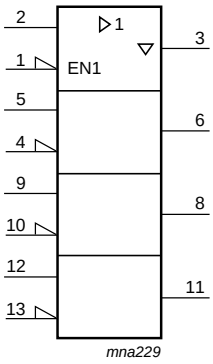


Fig 2. IEC logic symbol

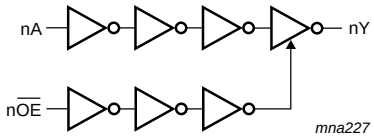


Fig 3. Logic diagram (one buffer)

5. Pinning information

5.1 Pinning

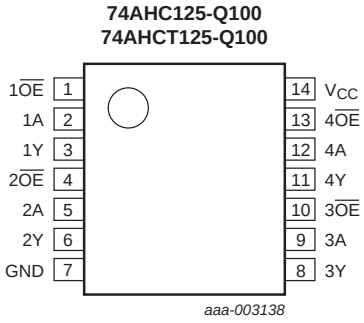
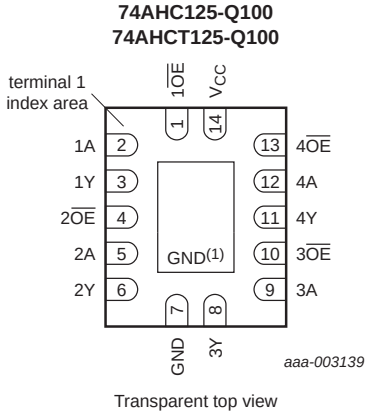


Fig 4. Pin configuration SO14 and TSSOP14



Transparent top view

(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN14

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}$, $2\overline{OE}$, $3\overline{OE}$, $4\overline{OE}$	1, 4, 10, 13	output enable input (active LOW)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V_{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Control	Input	Output
$n\overline{OE}$	nA	nY
L	L	L
	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
V_I	input voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1]	−20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	$V_O = -0.5$ V to (V_{CC} + 0.5 V)		-	±25	mA
I_{CC}	supply current			-	75	mA
I_{GND}	ground current			−75	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C				
	SO14 package		[2]	-	500	mW
	TSSOP14 package		[3]	-	500	mW
	DHVQFN14 package		[4]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC125-Q100			74AHCT125-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	+25	+125	−40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V_{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC125-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –50 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 μA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 50 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10.0	μA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	2.0	-	20	-	40	μA
C_I	input capacitance		-	3.0	10	-	10	-	10	pF
C_O	output capacitance		-	4.0	-	-	-	-	-	pF

Table 6. Static characteristics *…continued*

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHCT125-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	per input pin; V_I = V_{IH} or V_{IL}; V_{CC} = 5.5 V; I_O = 0 A V_O = V_{CC} or GND; other pins at V_{CC} or GND	-	-	±0.25	-	±2.5	-	±10.0	μA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	2.0	-	20	-	40	μA
ΔI_{CC}	additional supply current	per input pin; V_I = V_{CC} – 2.1 V; I_O = 0 A; other pins at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	3.0	10	-	10	-	10	pF
C_O	output capacitance		-	4.0	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC125-Q100											
t_{pd}	propagation delay	nA to nY; see Figure 6	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	4.4	8.0	1.0	9.5	1.0	11.5	ns
		C_L = 50 pF		-	6.2	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.0	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF		-	4.3	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 7	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C_L = 50 pF		-	6.8	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.3	5.1	1.0	6.0	1.0	6.5	ns
		C_L = 50 pF		-	4.7	7.1	1.0	8.0	1.0	9.0	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 7	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	6.7	9.7	1.0	11.5	1.0	12.5	ns
		C_L = 50 pF		-	9.6	13.2	1.0	15.0	1.0	16.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	4.8	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF		-	6.8	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	10	-	-	-	-	-	pF

Table 7. Dynamic characteristics *...continued*

GND = 0 V; For test circuit see Figure 8.

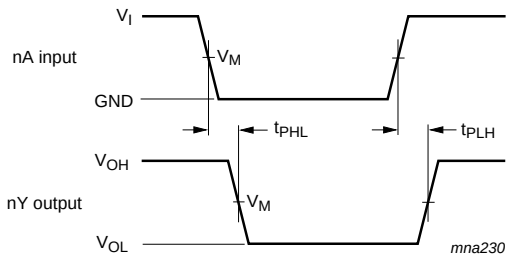
Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHCT125-Q100											
t_{pd}	propagation delay	nA to nY; see Figure 6	[2]								
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.0	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF		-	4.3	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 7									
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.4	5.1	1.0	6.0	1.0	6.5	ns
		C_L = 50 pF		-	4.9	7.3	1.0	8.3	1.0	9.5	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 7	[2]								
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF		-	6.5	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	12	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz, f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
N = number of inputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

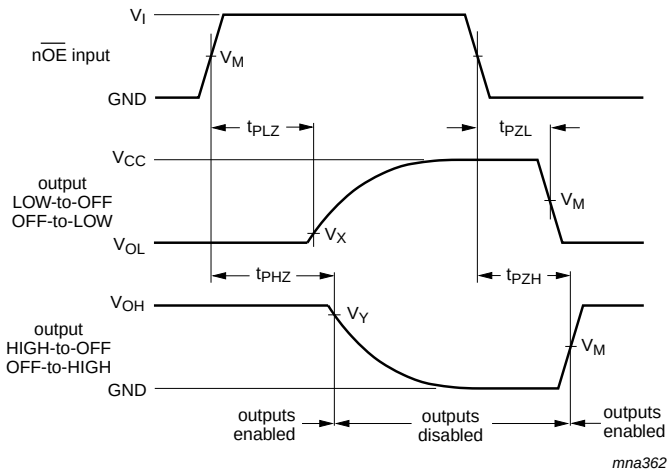
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay input (nA) to output (nY)



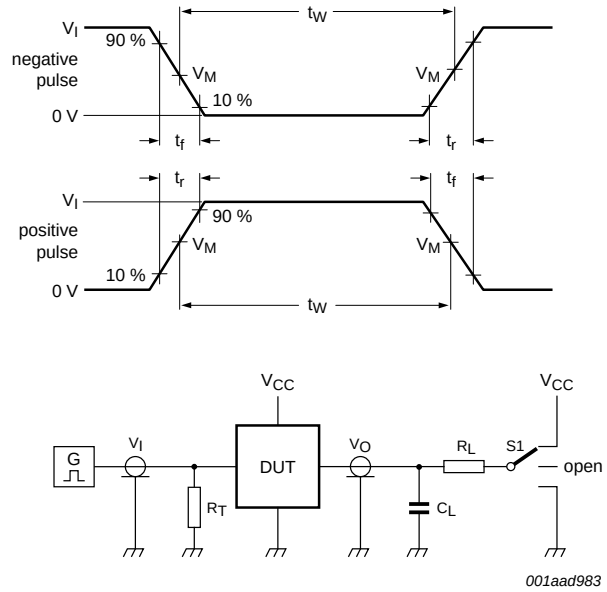
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Enable and disable times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC125-Q100	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OL} − 0.3 V
74AHCT125-Q100	1.5 V	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OL} − 0.3 V



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

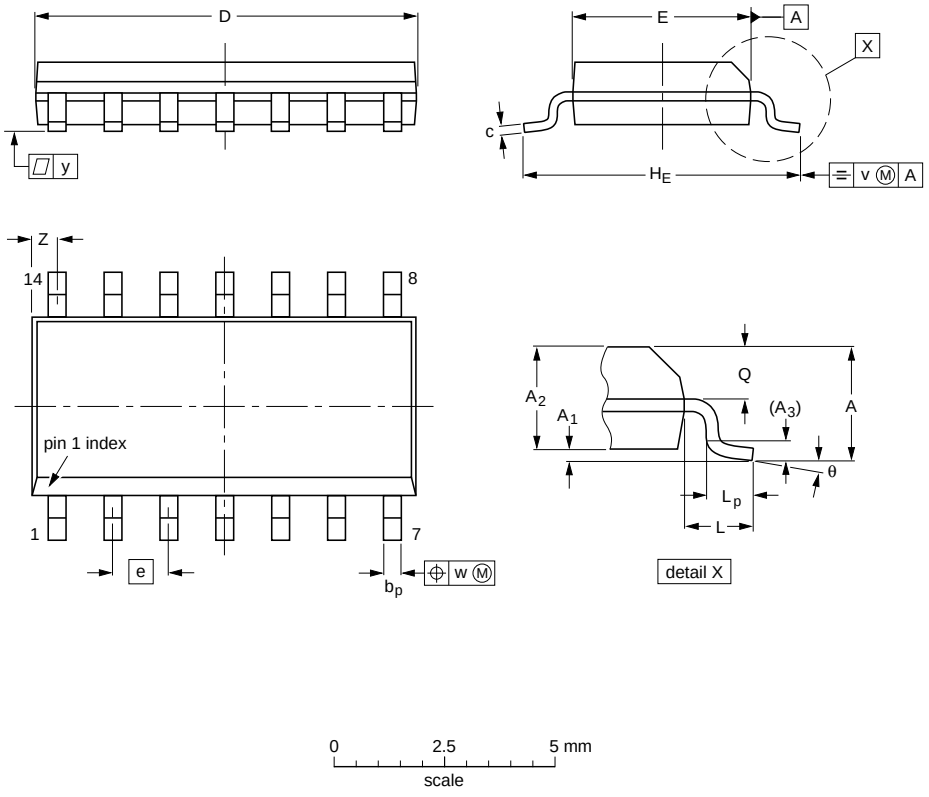
Fig 8. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC125-Q100	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74AHCT125-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

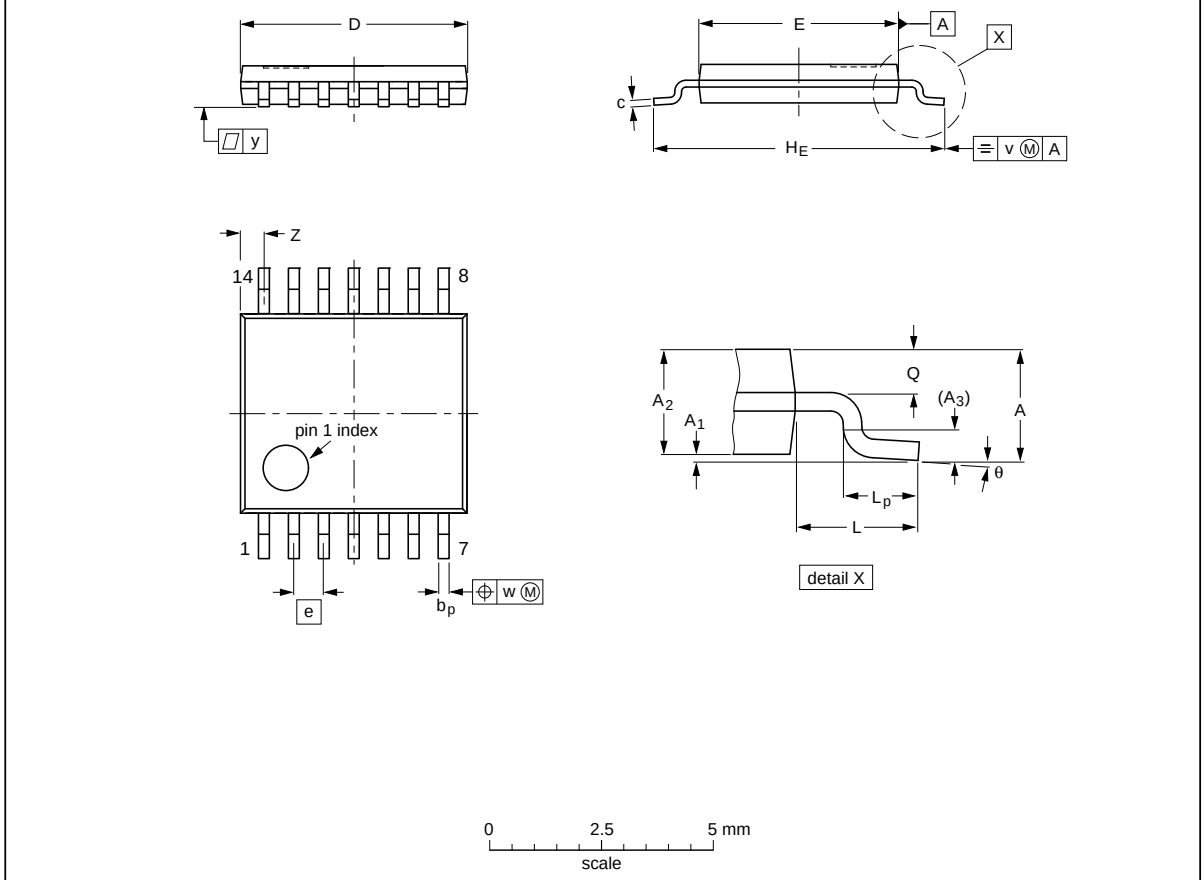
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm **SOT402-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

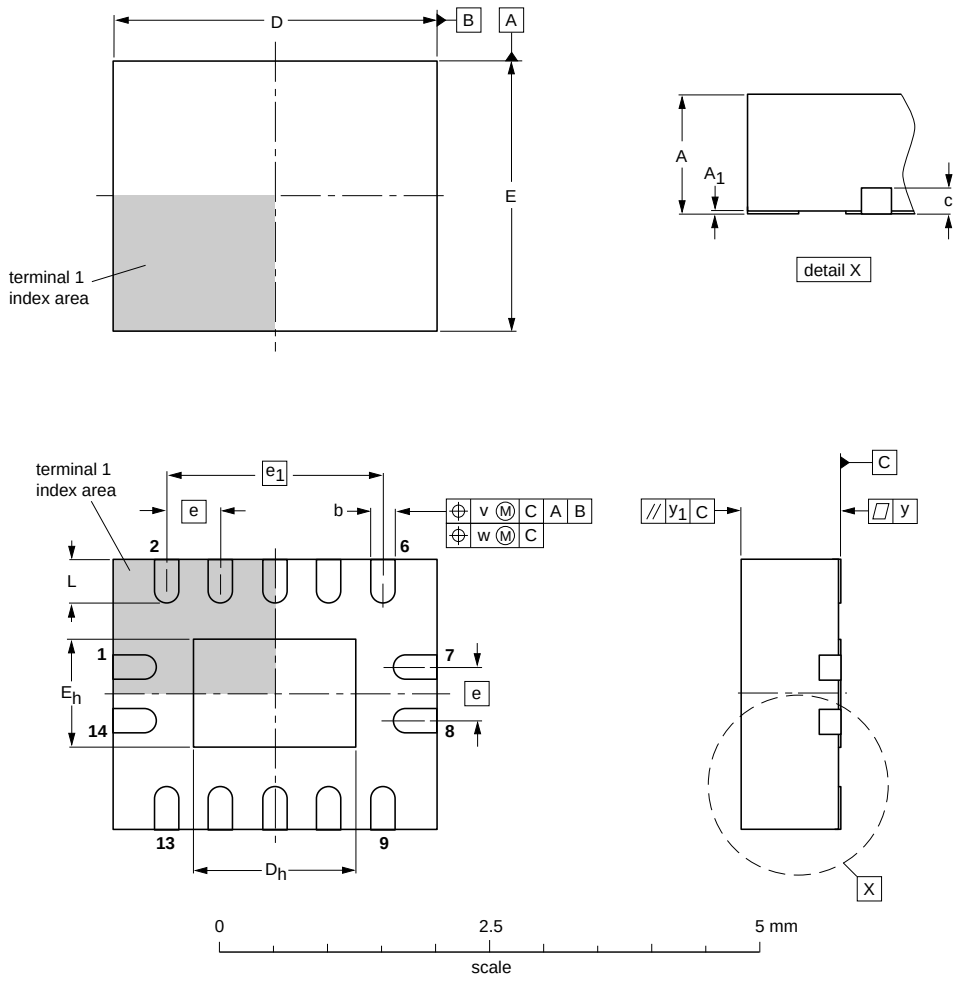
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT402-1		MO-153				~~99-12-27~~ 03-02-18

Fig 10. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm **SOT762-1**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max.	A_1	b	c	$D^{(1)}$	D_h	$E^{(1)}$	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.1 2.9	1.65 1.35	2.6 2.4	1.15 0.85	0.5	2	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT762-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 11. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
LSTTL	Low-power Schottky Transistor-Transistor Logic
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
CDM	Charge-Device Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT125_Q100 v.1	20120605	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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